1 6344888.pn.	L Number	Hits	Search Text	DB	Time stamp
1625 Insulat56 and moisture	-	1	6344888.pn.	USPAT	2002/11/05 09:54
10402 insulateS with moisture add 349/S.ccls. USPAT; JPO 2002/09/10 16:47 24 (insulateS with (silicon adj (nitride or oxide)) and (laminatS) USPAT; JPO 2002/10/15 14:31 USPAT; JPO 2002/10/15 14:34 USPAT; JPO 2002/10/15 15:11 USPAT; JPO 2002/10/15 15:12 USPAT; JPO 2002/10/15 15:13 U	-	46263	insulat\$6 and moisture	USPAT; JPO	2002/09/10 10:18
- 43 (insulates with moisture) and 349/S.ccls. USPAT; JPO 2003/05/15 16:47	-	10402	insulat\$6 with moisture	USPAT: JPO	
24 (insults6 with (silicon adj (nitride or oxide)) and (laminat5)	_	43	(insulat\$6 with moisture) and 349/\$.ccls.		
Oxide) and laminat\$\(1 \) and (laminat\$\(1 \) silicon adj (nitride or oxide)) and (laminat\$\(1 \) same (silicon adj (nitride or oxide)) and (laminat\$\(1 \) same (silicon adj (nitride or oxide)) and (laminat\$\(1 \) same (silicon adj (nitride or oxide)) and (laminat\$\(1 \) sort stack and periphery and (laminat\$\(1 \) sort stack and periphery and ((semiconductor or silicon) adj substrate)	-	24			
1					
oxide) and (laminat\$5 or stack)	-	34		USPAT: JPO	2003/05/15 16:47
3883 ((insults6 or dielectric) same (silicon adj (intride or oxide)) and (laminat5s or stack) 3050 ((insults6 or dielectric) with (silicon adj (intride or oxide))) and (laminat5s or stack) 3050 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 36 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 37 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 37 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 37 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 37 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide))) and (laminat5s or stack) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (silicon adj (intride or oxide)) 38 ((insults6 or dielectric) near (insults6 or dielectric) 38 ((insults6 or dielectric) near (insults6 or dielectric) 38 ((insults6 or dielectric) 38 ((insult					,,
Initride or oxide) 3 and (laminat\$5 or stack)	_	3883		USPAT: JPO	2002/10/15 14:34
Stack 3050 (insult\$6 or dielectric) with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) 36 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and periphery and ((semiconductor or silicon) adj substrate) 37 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and periphery 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and periphery 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and periphery 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (nitride or oxide)) and (laminat\$5 or stack) 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) 375 ((insult\$6 or dielectric) near (silicon adj (nitride or oxide)) 375 ((insult\$6 or oxide				3521117, 525	2002, 20, 20 21.01
(intride or oxide)) and (laminat\$5 or stack)		Ì			
(intride or oxide)) and (laminat\$5 or stack)	_	3050	((insult\$6 or dielectric) with (silicon adi	USPAT: JPO	2002/10/15 14:34
stack 36				0011117, 010	2002, 10, 13 11.31
36					
(intride or oxide)) and (laminat\$S or stack) and periphery and ((semiconductor or silicon) adj substrate)	_	36	1 .	USPAT: JPO	2002/10/15 14:40
Stack) and periphery and ((semiconductor or slicion) adj substrate)				3333117, 333	=====================================
Silicon adj substrate					
Company Comp					
(nitride or oxide)) and (laminat\$5 or stack) and periphery	_	51		USPAT: JPO	2002/10/15 14:39
Stack and periphery ((insult56 or dielectric) near (silicon adj (nitride or oxide)) and (laminat\$5 or stack)					
375					
(nitride or oxide)) and (laminat\$5 or stack)	-	375		USPAT; JPO	2002/10/15 15:11
14					, , == == :==
Cnitride or oxide) and (laminat\$5 or stack) and (liquid adj crystal)					
Cnitride or oxide)) and (laminat\$5 or stack) and (liquid adj crystal) ("362360" "3910681" "4024626" USPAT 2002/10/15 15:13 "4040727" "4073571" "4103297" "4185894" "4191528" "4239346" "4382658" "4431271" "4470060" "4602850" "4821244" "4839707" "4856019" "5007710" "5056895" "5159476" "521447" "45254020" "5365355" "5365622" "5365355" "5395662" "5467216" "53760867" "5760863" "5760861" "5760	-	14		USPAT; JPO	2002/10/15 15:12
Stack) and (liquid adj crystal)				•	, ,
"4073571" "4073571" "4103297" "4185894" "4191452" "429346" "4382658" "4431271" "447060" "4602850" "4822144" "4839707" "4856019" "5007710" "5056895" "5159476" "5218472" "5254202" "5365355" "5395662" "5473488" "5497025" "5523620" "5568052" "5568052" "5568052" "5568052" "5568052" "5568052" "5760607" "5760853" "5760981" "5766067" "5760853" "58829570" "5978056").PN. - 1 6 6124912.pn 3 (insulat\$6 with moisture) and 349/\$.ccls (insulat\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 4 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 5 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 6 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 8 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 16 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 17 (passivation near10 (reflect\$4 metal pixel)) - 18 (passivation near10 (reflect\$4 metal pixel)) - 18 (passivation near10 (reflect\$4 metal pixel)) - 18 (passivation near10 (reflect\$4 metal pixel))			stack)and (liquid adj crystal)		
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"4382658" "4431271" "447060" "4602850" "4802144" "4839707" "4856019" "5007710" "5056895" "5159476" "5218472" "5254202" "5365355" "53956627" "5461501" "5467216" "5473448" "5497025" "558031" "5760931" "5760931" "5760931" "5760931" "5760931" "5760931" "5784324" "5798805" "5889570" "5978056").PN. - 1 63 (insulat\$6 with moisture) and 349/\$.ccls. USPAT USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J			"4040727" "4073571" "4103297"		
"4602850" "4822144" "4839707" "4856019" "50067710" "5056895" "5159476" "5218472" "5224202" "5365355" "5395662" "5461501" "5467216" "5473448" "5497025" "5563231" "5760667" "5760853" "5760821" "5760867" "5760853" "5828493" "5838715" "5889570" "5978056").PN. - 1 63 (insulat\$6 with moisture) and 349/\$.ccls. - 368 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 5 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 5 6 6 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 6 7 7 8 8 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9					
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"5467216" "5473448" "5497025" "5523862" "5570213" "5548860" "5580231" "5760667" "57648860" "5760981" "5760324" "5798805" "5828493" "5834103" "5838715" "5828493" "5978056").PN.			"5159476" "5218472" "5254202"		
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- 1 63 "5889570" "5978056").PN. 6124912.pn. (insulat\$6 with moisture) and 349/\$.ccls. USPAT USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;					
- 1 6124912.pn. (insulat\$6 with moisture) and 349/\$.ccls. - 68 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 5 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 6 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 6 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 7 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$6 with (silicon adj (nitride or oxide)) and (laminat\$6 with (silicon adj (nitride or oxide)) and (laminat\$6 with (silicon adj (nitride or oxide)) and (lamina					
- 63 (insulat\$6 with moisture) and 349/\$.ccls. Comparison		_	· ·		
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68 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;	ļ -	6.3	(insulative with moisture) and 349/\$.ccis.	· ·	2003/05/15 16:47
- 68 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 4 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				· ·	
- 68 (insult\$6 with (silicon adj (nitride or oxide)) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 - 1650 349/113 18M_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) - 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 - 1650 349/113 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12 2004/06/04 14:12				•	
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4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) 4 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) 1650 349/113 EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; (passivation near10 (reflect\$4 metal pixel)) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J		.00		•	2004/06/04 14:12
- 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			Onlde, / / and (laminates of Stack)		
- 4 (insult\$6 with (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack) and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 1BM_TDB					
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(passivation near10 (reflect\$4 metal pixel)) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		•		·	2004/05/20 13:31
- 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			(brootington mentio (refrect), mergi hixel))		
- 46 (insult\$6 and (silicon adj (nitride or oxide))) and (laminat\$5 or stack)and (passivation near10 (reflect\$4 metal pixel)) - 1650 349/113 USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
oxide))) and (laminat\$5 or stack)and (US-PGPUB; (passivation near10 (reflect\$4 metal pixel)) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT;	_	46	(insult\$6 and (silicon adi (nitride or	_	2004/06/04 14:12
(passivation near10 (reflect\$4 metal pixel))					
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;		-		, ,	
- 1650 349/113 IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;					
- 1650 349/113 USPAT; US-PGPUB; EPO; JPO; DERWENT;					
US-PGPUB; EPO; JPO; DERWENT;	-	1650	349/113	_	2004/06/04 14:10
EPO; JPO; DERWENT;				US-PGPUB;	
DERWENT;				EPO; JPO;	
IBM TDB				DERWENT;	
				IBM_TDB	

-	1329	349/138	USPAT;	2004/06/04 14:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2268	349/42	USPAT;	2004/06/04 14:11
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
	1523	349/43	IBM_TDB USPAT;	2004/06/04 14:11
-	1523	349/43	US-PGPUB;	2004/06/04 14:11
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1409	349/153	USPAT;	2004/06/04 14:11
		0 07, 200	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2		USPAT;	2004/06/04 14:11
		oxide))) and (laminat\$5 or stack)and	US-PGPUB;	
1		(passivation near10 (reflect\$4 metal pixel))	EPO; JPO;	
1		and 349/113	DERWENT;	
	_		IBM_TDB	
-	0	(insult\$6 with (silicon adj (nitride or	USPAT;	2004/06/04 14:12
		oxide))) and (laminat\$5 or stack)and 349/113	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
_	2	(insult\$6 and (silicon adj (nitride or	USPAT;	2004/06/04 14:12
		oxide))) and (laminat\$5 or stack)and	US-PGPUB;	2001,00,01 11.12
		(passivation near10 (reflect\$4 metal pixel))	EPO; JPO;	
		and 349/138	DERWENT;	
			IBM_TDB	
-	3		USPAT;	2004/06/04 14:12
Ì		oxide))) and (laminat\$5 or stack)and	US-PGPUB;	
		(passivation near10 (reflect\$4 metal pixel))	EPO; JPO;	
		and 349/42	DERWENT;	
		(1) 7,44 . 7 (13)	IBM_TDB	0004/06/04 54 55
_	8	(insult\$6 and (silicon adj (nitride or	USPAT;	2004/06/04 14:13
		oxide))) and (laminat\$5 or stack)and	US-PGPUB; EPO; JPO;	
		(passivation near10 (reflect\$4 metal pixel)) and 349/43	DERWENT;	
		MIM 317/13	IBM TDB	
-	o	(insult\$6 and (silicon adj (nitride or	USPAT;	2004/06/04 14:13
		oxide))) and (laminat\$5 or stack)and	US-PGPUB;	
		(passivation near10 (reflect\$4 metal pixel))	EPO; JPO;	
	i	and 349/153	DERWENT;	
			IBM_TDB	
-	1633	(refractive adj index) near10 ((silicon adj	USPAT;	2004/08/17 16:56
		oxide) or (silicon adj nitride))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(IBM_TDB	2004/00/27 25
-	53	(refractive adj index) near10 ((silicon adj	USPAT;	2004/08/17 16:57
		oxide) or (silicon adj nitride)) and	US-PGPUB;	
		349/\$.ccls.	EPO; JPO; DERWENT;	
1			IBM TDB	
L	L		TDM IDD	1